

## 1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients. This triac will commutate the full RMS current at the maximum rated junction temperature ( $T_{J(max)} = 150^\circ\text{C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

## 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability
- Full cycle AC conduction
- Isolated mounting base package
- Less sensitive gate for high noise immunity
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Triggering in three quadrants only
- Very high immunity to false turn-on by  $dV/dt$

## 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature

## 4. Quick reference data

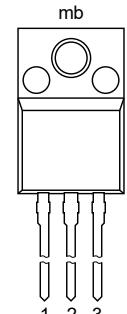
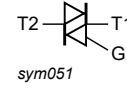
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 88^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	10	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{J(init)} = 25^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	90	A
		full sine wave; $T_{J(init)} = 25^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$	-	-	99	A

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$T_j$	junction temperature			-	-	150	°C
$V_{PP}$	peak pulse voltage	$T_j = 25^\circ\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>		-	-	2	kV
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	-	55	mA
$V_T$	on-state voltage	$I_T = 14.1\text{ A}$ ; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	1.3	1.5	V
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25^\circ\text{C}$		850	-	-	V
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 150^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit		1000	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 150^\circ\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit		4	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated	 <b>TO-220F (SOT186A)</b>	

## 6. Ordering information

Table 3. Ordering information

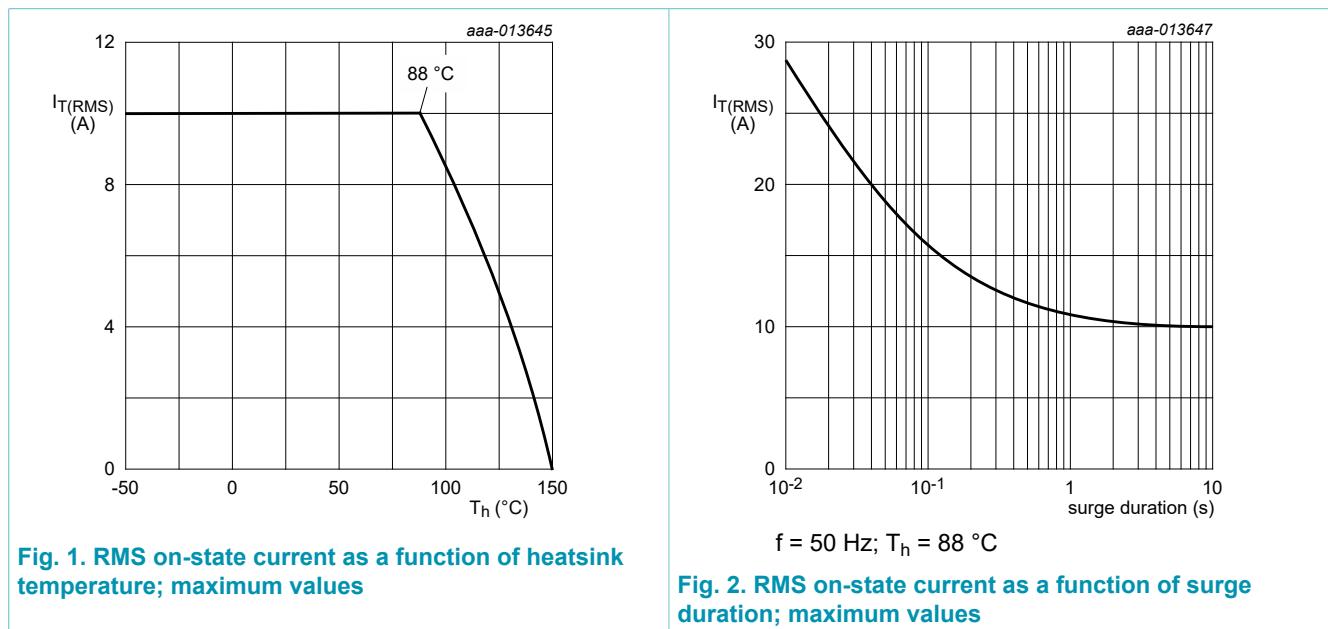
Type number	Package		
	Name	Description	Version
ACTT10X-800CT	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage			-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 88^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		-	10	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>		-	90	A
		full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$		-	99	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse		-	40	$\text{A}^2\text{s}$
$dI_T/dt$	rate of rise of on-state current	$I_G = 0.2\text{ A}$		-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current	$t = 20\text{ }\mu\text{s}$		-	2	A
$P_{GM}$	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
$T_{stg}$	storage temperature			-40	150	$^\circ\text{C}$
$T_j$	junction temperature			-	150	$^\circ\text{C}$
$V_{PP}$	peak pulse voltage	$T_j = 25^\circ\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>		-	2	kV



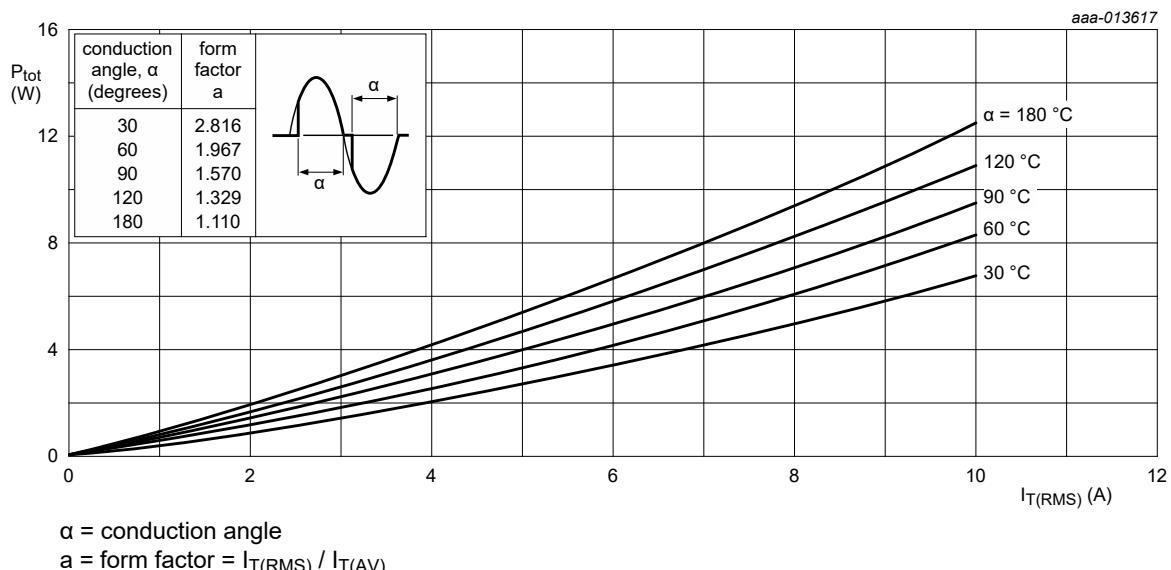


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

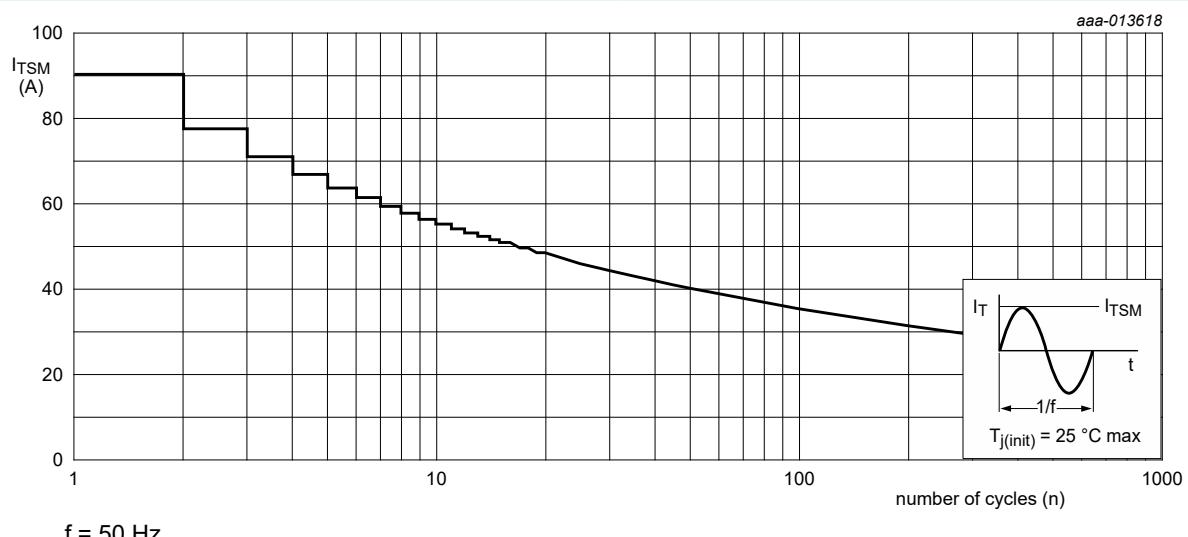


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

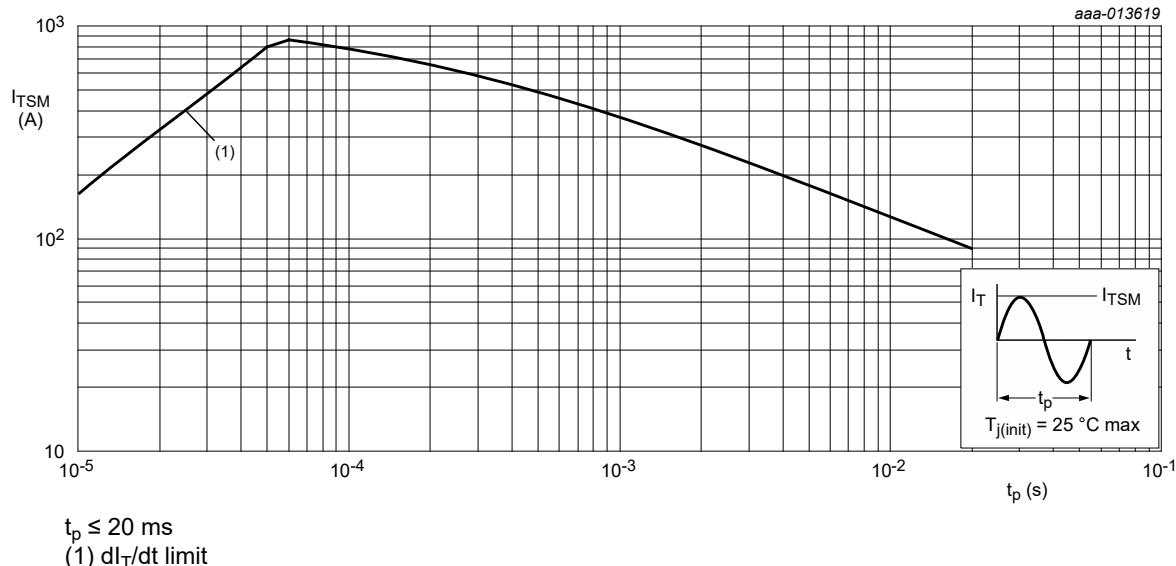


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

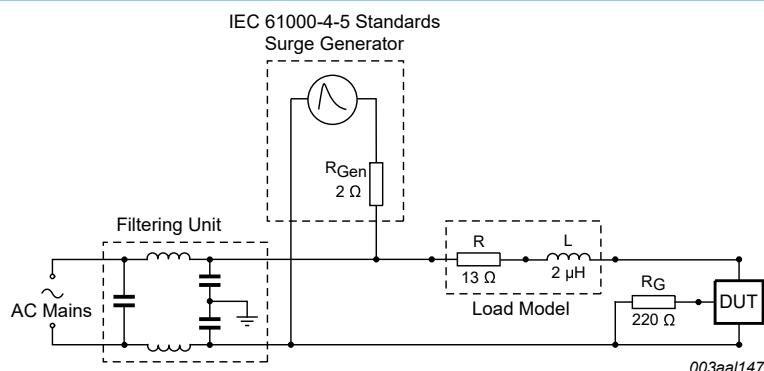


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle; with heatsink compound; <a href="#">Fig. 7</a>	-	-	2.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

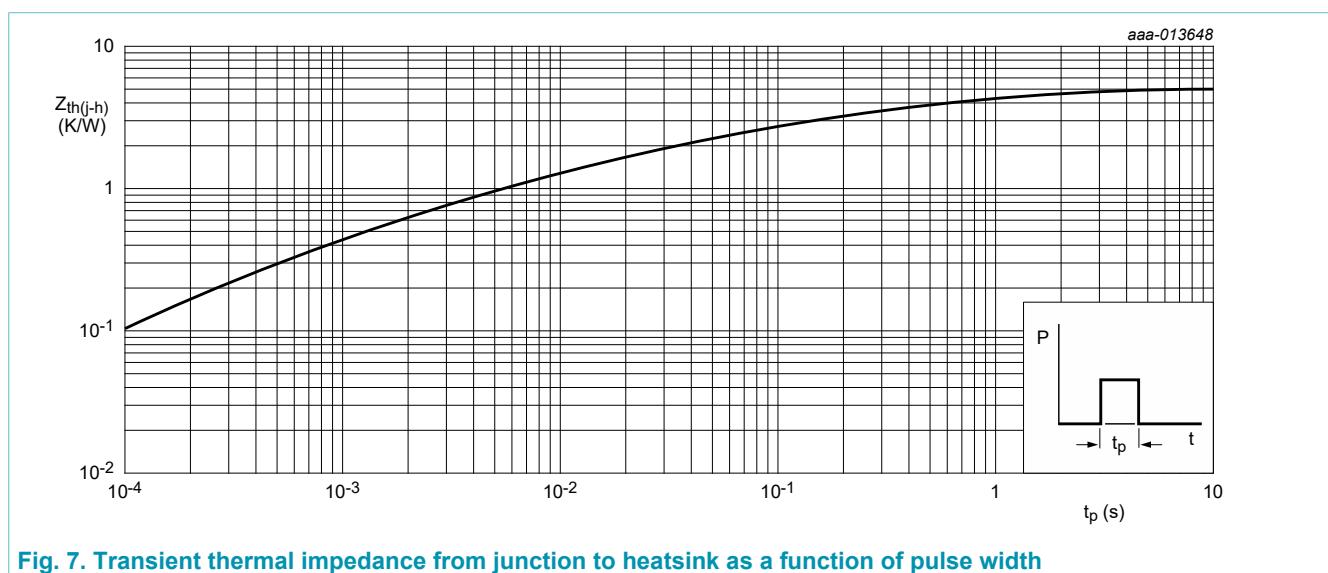


Fig. 7. Transient thermal impedance from junction to heatsink as a function of pulse width

## 9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50$ Hz $\leq$ $f \leq$ $60$ Hz; $T_h = 25$ °C	-	-	2500	V
$C_{isol}$	isolation capacitance	from main terminal 2 to external heatsink; $f = 1$ MHz; $T_h = 25$ °C	-	10	-	pF

## 10. Characteristics

**Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; LD+ G+; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; LD+ G-; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
		$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; LD- G-; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	-	35	mA
$I_L$	latching current	$V_D = 12 \text{ V}$ ; $I_G = 100 \text{ mA}$ ; LD+ G+; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>		-	-	70	mA
		$V_D = 12 \text{ V}$ ; $I_G = 100 \text{ mA}$ ; LD+ G-; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>		-	-	70	mA
		$V_D = 12 \text{ V}$ ; $I_G = 100 \text{ mA}$ ; LD- G-; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>		-	-	70	mA
$I_H$	holding current	$V_D = 12 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	-	55	mA
$V_T$	on-state voltage	$I_T = 14.1 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>		-	1	1.2	V
		$V_D = 400 \text{ V}$ ; $I_T = 100 \text{ mA}$ ; $T_j = 150 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>		0.2	0.4	-	V
$I_D$	off-state current	$V_D = 800 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$		-	-	10	$\mu\text{A}$
		$V_D = 800 \text{ V}$ ; $T_j = 150 \text{ }^\circ\text{C}$		-	-	0.5	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1 \text{ mA}$ ; $t_p = 1 \text{ ms}$ ; $T_j = 25 \text{ }^\circ\text{C}$		850	-	-	V
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536 \text{ V}$ ; $T_j = 150 \text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit		1000	-	-	V/ $\mu\text{s}$
$dl_{com}/dt$	rate of change of commutating current	$V_D = 400 \text{ V}$ ; $T_j = 150 \text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 10 \text{ A}$ ; $dV_{com}/dt = 20 \text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit		4	-	-	A/ms

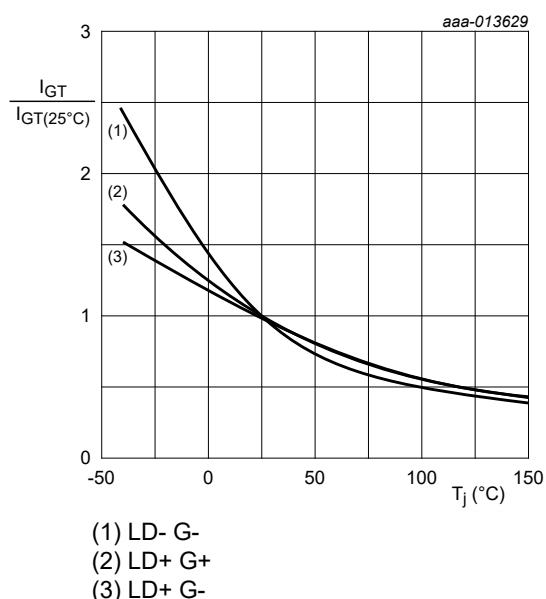


Fig. 8. Normalized gate trigger current as a function of junction temperature

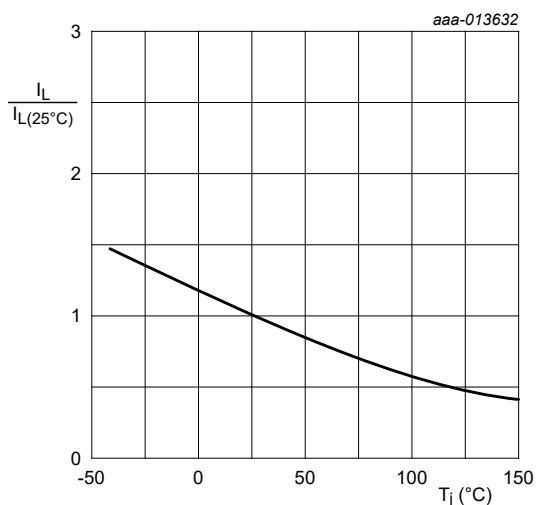


Fig. 9. Normalized latching current as a function of junction temperature

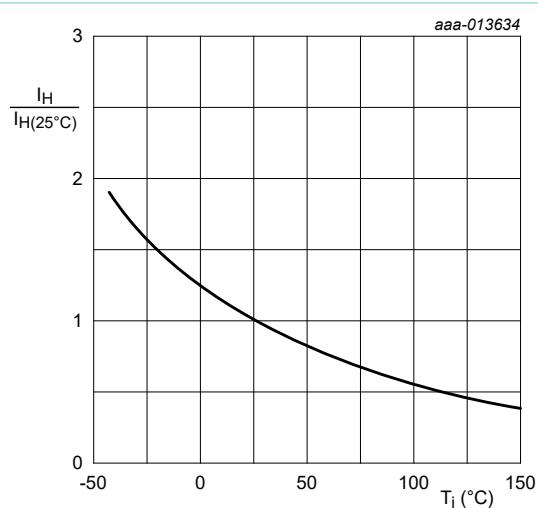


Fig. 10. Normalized holding current as a function of junction temperature

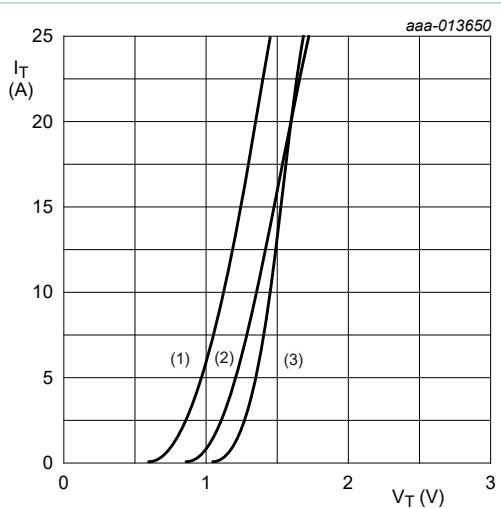


Fig. 11. On-state current as a function of on-state voltage

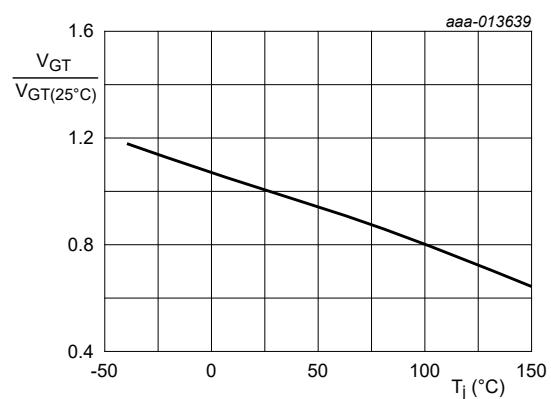
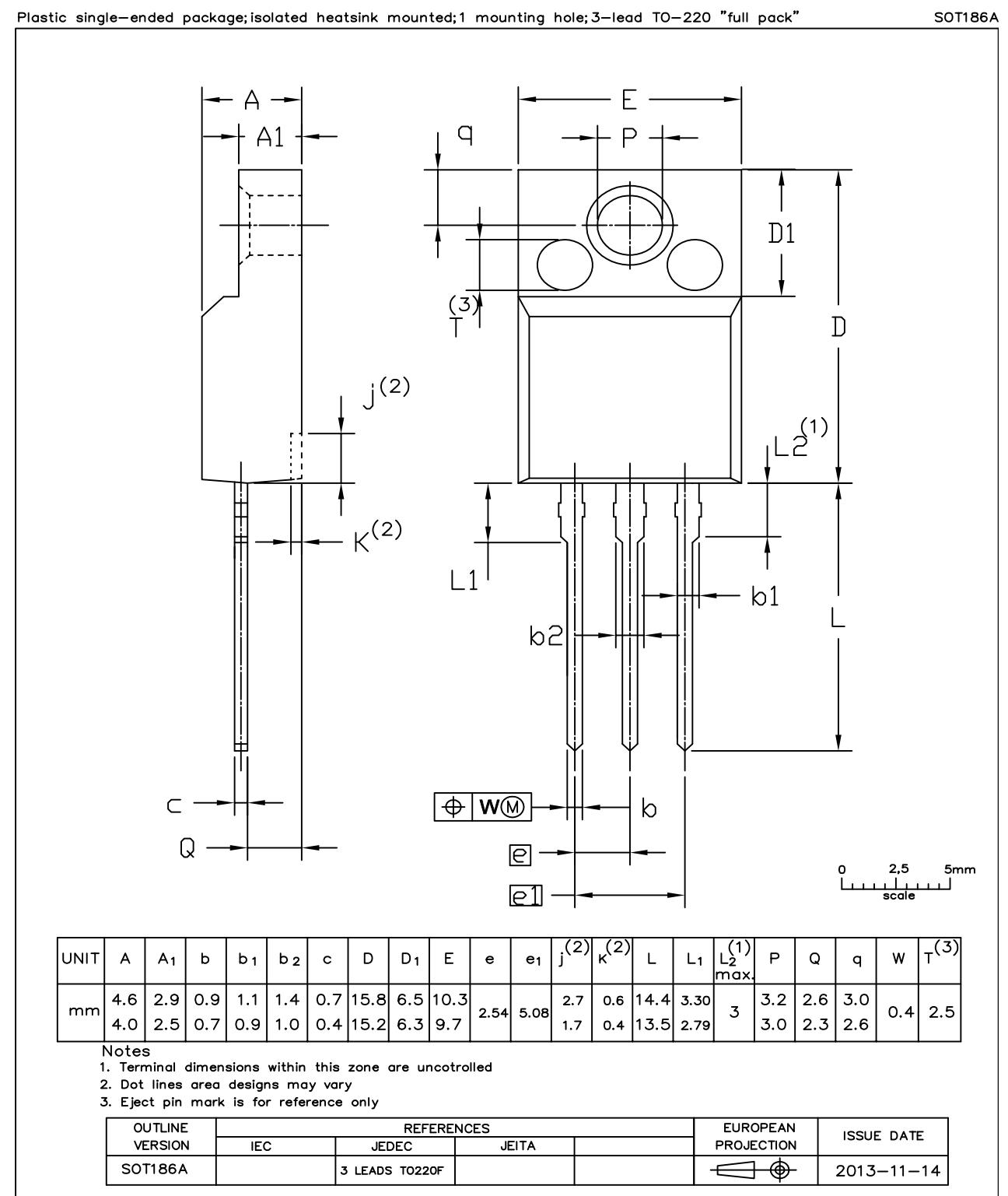


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

## 11. Package outline



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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